ABSTRACT

There is provided a technique that includes: (a) supplying a first gas containing hydrogen and oxygen to a substrate in a process chamber; (b) supplying a second gas containing nitrogen and hydrogen to the substrate; (c) supplying a third gas containing a halogen element to the substrate; (d) supplying a reaction gas to the substrate; (e) performing (a) and (b); and (f) forming a film on the substrate by performing (c) and (d) after performing (e).

FIG. 4